



4N29, 4N30, 4N31, 4N32, 4N33

## OPTICALLY COUPLED ISOLATOR PHOTODARLINGTON OUTPUT



### DESCRIPTION

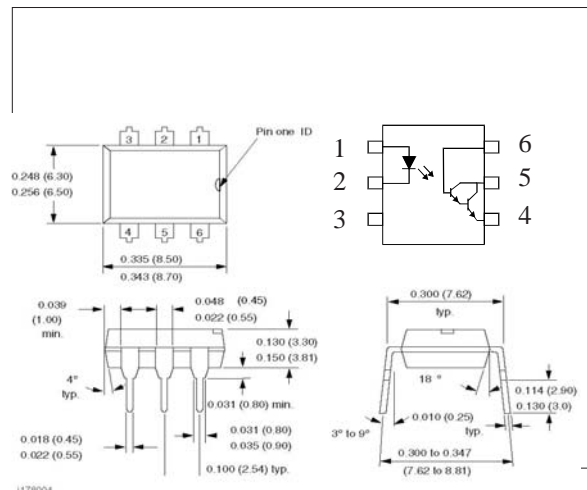
The 4N29, 4N30, 4N31, 4N32, 4N33 series of optically coupled isolators consist of an infrared light emitting diode and NPN silicon photodarlington in a space efficient dual in line plastic package.

### FEATURES

- Options :-  
10mm lead spread - add G after part no.  
Surface mount - add SM after part no.  
Tape&reel - add SMT&R after part no.
- High Current Transfer Ratio
- High Isolation Voltage (5.3kV<sub>RMS</sub>, 7.5kV<sub>PK</sub>)
- All electrical parameters 100% tested
- Custom electrical selections available

### APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances



### ABSOLUTE MAXIMUM RATINGS (25°C unless otherwise specified)

Storage Temperature \_\_\_\_\_ -55°C to + 150°C  
 Operating Temperature \_\_\_\_\_ -55°C to + 100°C  
 Lead Soldering Temperature  
 (1/16 inch (1.6mm) from case for 10 secs) 260°C

### INPUT DIODE

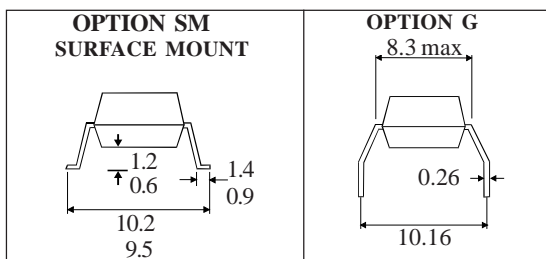
Forward Current \_\_\_\_\_ 80mA  
 Reverse Voltage \_\_\_\_\_ 5V  
 Power Dissipation \_\_\_\_\_ 100mW

### OUTPUT TRANSISTOR

Collector-emitter Voltage BV<sub>CEO</sub> \_\_\_\_\_ 30V  
 Collector-base Voltage BV<sub>CBO</sub> \_\_\_\_\_ 50V  
 Emitter-collector Voltage BV<sub>ECO</sub> \_\_\_\_\_ 5V  
 Power Dissipation \_\_\_\_\_ 150mW

### POWER DISSIPATION

Total Power Dissipation \_\_\_\_\_ 250mW  
 (derate linearly 3.3mW/°C above 25°C)



### ISOCOM COMPONENTS 2004 LTD

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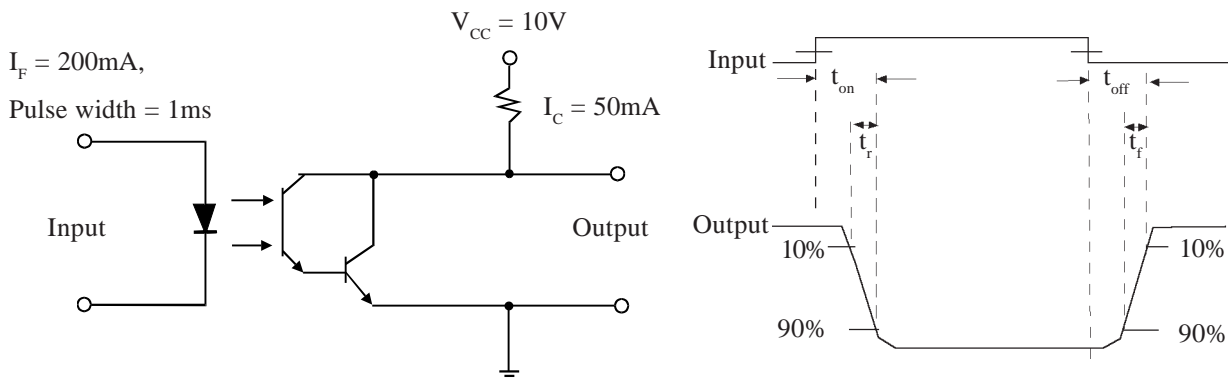
**ELECTRICAL CHARACTERISTICS (  $T_A = 25^\circ\text{C}$  Unless otherwise noted )**

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage ( $V_F$ )		1.2	1.5	V	$I_F = 50\text{mA}$
	Reverse Current ( $I_R$ )			10	$\mu\text{A}$	$V_R = 6\text{V}$
Output	Collector-emitter Breakdown ( $BV_{CE0}$ )	30			V	$I_C = 1\text{mA}$ (note 2)
	Collector-base Breakdown ( $BV_{CBO}$ )	50			V	$I_C = 100\mu\text{A}$
	Emitter-collector Breakdown ( $BV_{ECO}$ )	5			V	$I_E = 100\mu\text{A}$
	Collector-emitter Dark Current ( $I_{CEO}$ )			100	nA	$V_{CE} = 10\text{V}$
Coupled	Collector Output Current ( $I_C$ ) (Note 2)					
	4N32, 4N33	50			mA	$10\text{mA } I_F, 10\text{V } V_{CE}$
	4N29, 4N30	10			mA	$10\text{mA } I_F, 10\text{V } V_{CE}$
	4N31	5			mA	$10\text{mA } I_F, 10\text{V } V_{CE}$
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$					
	4N29, 4N30, 4N32, 4N33			1.0	V	$8\text{mA } I_F, 2\text{mA } I_C$
	4N31			1.2	V	$8\text{mA } I_F, 2\text{mA } I_C$
	Input to Output Isolation Voltage $V_{ISO}$	5300			$V_{RMS}$	(note 1)
		7500			$V_{PK}$	(note 1)
	Input-output Isolation Resistance $R_{ISO}$	$5 \times 10^{10}$			$\Omega$	$V_{IO} = 500\text{V}$ (note 1)
Output Turn on Time $t_{on}$			5	$\mu\text{s}$	$V_{CC} = 10\text{V}, I_C = 50\text{mA},$ $I_F = 200\text{mA},$ Pulse Width = 1ms fig.1	
Output Turn off Time $t_{off}$						
4N32, 4N33	$t_{off}$		100	$\mu\text{s}$		
4N29, 4N30, 4N31			40	$\mu\text{s}$		

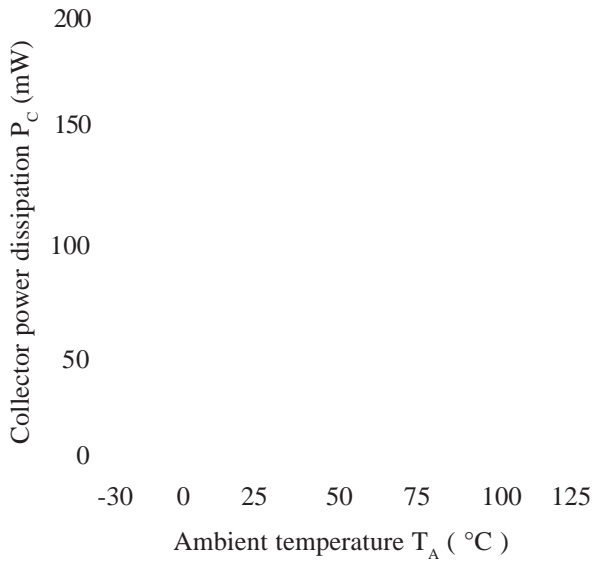
Note 1 Measured with input leads shorted together and output leads shorted together.

Note 2 Special Selections are available on request. Please consult the factory.

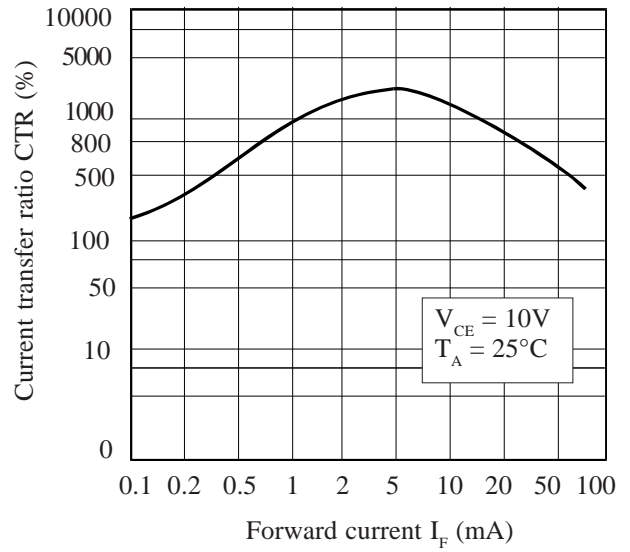
**FIGURE 1**



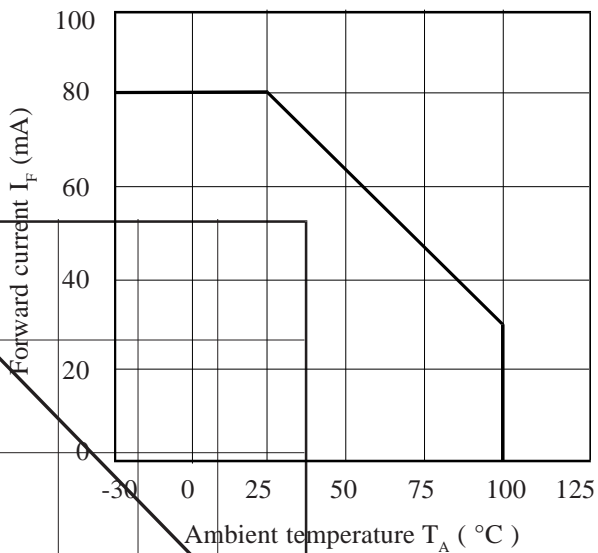
**Collector Power Dissipation vs. Ambient Temperature**



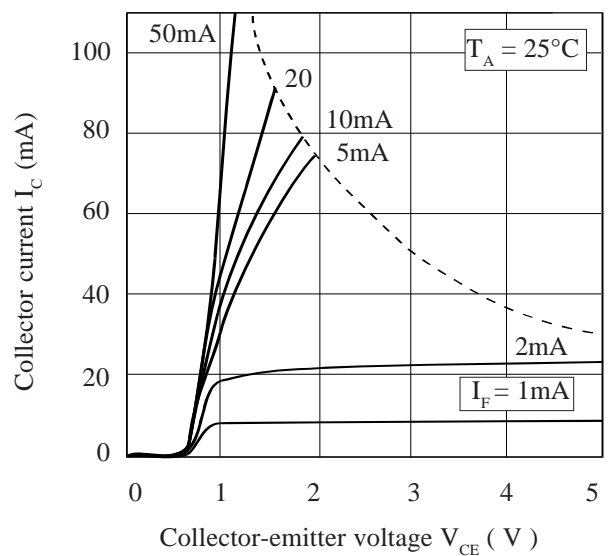
**Current Transfer Ratio vs. Forward Current**



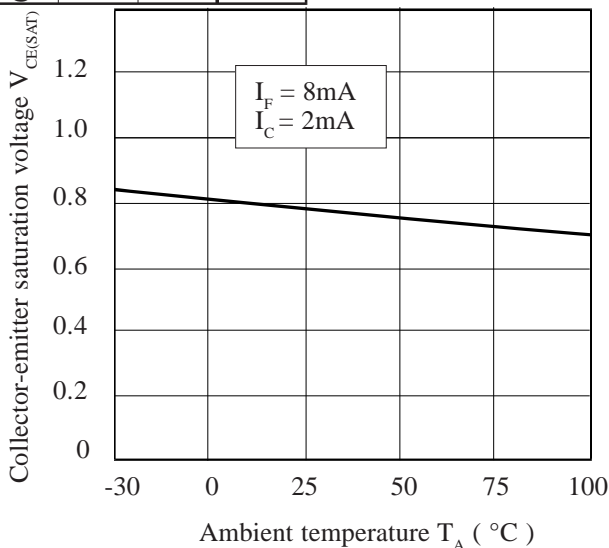
**Forward Current vs. Ambient Temperature**



**Collector Current vs. Collector-emitter Voltage**



**Collector-emitter Saturation Voltage vs. Ambient Temperature**



**Relative Current Transfer Ratio vs. Ambient Temperature**

